DISCRETE POWER DIODES and THYRISTORS

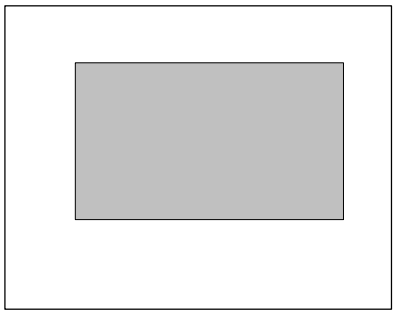
DATA BOOK

International
IOR Rectifier

ST780C..L SERIES

PHASE CONTROL THYRISTORS **Hockey Puk Version**

1350A



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ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM}, max. repetitive peak and off-state voltage V	V_{RSM}, maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_J$ max mA
ST780C..L	04	400	500	80
	06	600	700	

On-state Conduction

Parameter		ST780C..L	Units	Conditions		
$I_{T(AV)}$	Max. average on-state current	1350 (500)	A	180° conduction, half sine wave		
	@ Heatsink temperature	55 (85)	°C	double side (single side) cooled		
$I_{T(RMS)}$	Max. RMS on-state current	2700	A	DC @ 25°C heatsink temperature double side cooled		
I_{TSM}	Max. peak, one-cycle non-repetitive surge current	24400	A	t = 10ms	No voltage reapplied	Sinusoidal half wave, Initial $T_J = T_J$ max.
		25600		t = 8.3ms		
		20550		t = 10ms	100% V_{RRM} reapplied	
		21500		t = 8.3ms		
I^2t	Maximum I^2t for fusing	2986	KA^2s	t = 10ms	No voltage reapplied	
		2726		t = 8.3ms		
		2112		t = 10ms	100% V_{RRM} reapplied	
		1928		t = 8.3ms		
$I^2\sqrt{t}$	Maximum $I^2\sqrt{t}$ for fusing	29860	$KA^2\sqrt{s}$	t = 0.1 to 10ms, no voltage reapplied		
$V_{T(TO)1}$	Low level value of threshold voltage	0.80	V	(16.7% x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ max.		
$V_{T(TO)2}$	High level value of threshold voltage	0.90		(I > π x $I_{T(AV)}$), $T_J = T_J$ max.		
r_{t1}	Low level value of on-state slope resistance	0.14	mΩ	(16.7% x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ max.		
r_{t2}	High level value of on-state slope resistance	0.13		(I > π x $I_{T(AV)}$), $T_J = T_J$ max.		
V_{TM}	Max. on-state voltage	1.31	V	I_{pk}= 3600A, $T_J = T_J$ max, t_p = 10ms sine pulse		
I_H	Maximum holding current	600	mA	T_J = 25°C, anode supply 12V resistive load		
I_L	Typical latching current	1000				

Switching

Parameter		ST780C..L	Units	Conditions
di/dt	Max. non-repetitive rate of rise of turned-on current	1000	A/µs	Gate drive 20V, 20Ω, $t_r \leq 1\mu s$ $T_J = T_J$ max, anode voltage ≤ 80% V_{DRM}
t_d	Typical delay time	1.0	µs	Gate current 1A, di_g/dt = 1A/µs V_d = 0.67% V_{DRM}, T_J = 25°C
t_q	Typical turn-off time	150		I_{TM} = 750A, $T_J = T_J$ max, di/dt = 60A/µs, V_R = 50V dv/dt = 20V/µs, Gate 0V 100Ω, t_p = 500µs

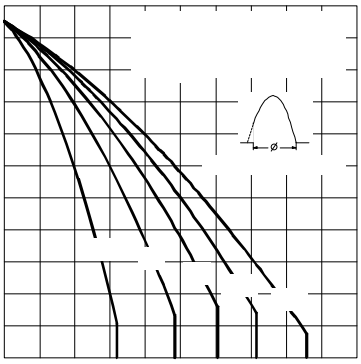


Fig. 3 - Current Ratings Characteristics

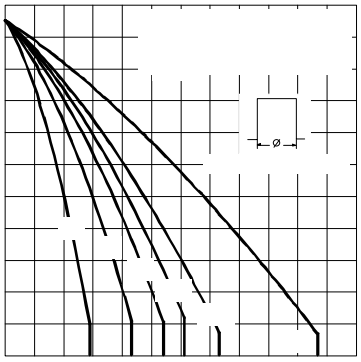


Fig. 4 - Current Ratings Characteristics

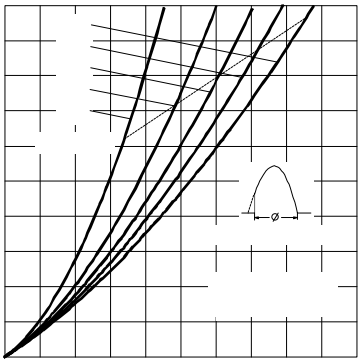


Fig. 5- On-state Power Loss Characteristics

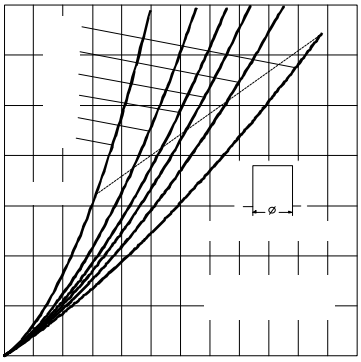


Fig. 6- On-state Power Loss Characteristics

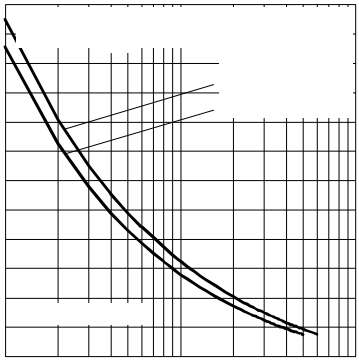


Fig. 7 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

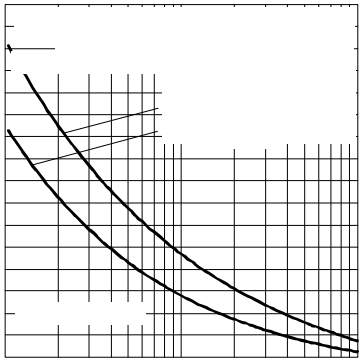


Fig. 8 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

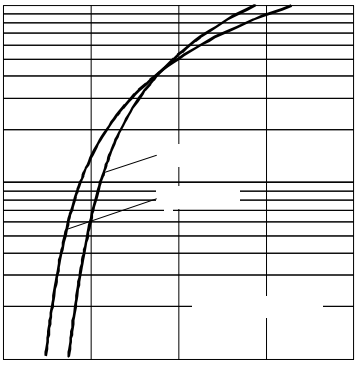


Fig. 9 - On-state Voltage Drop Characteristics

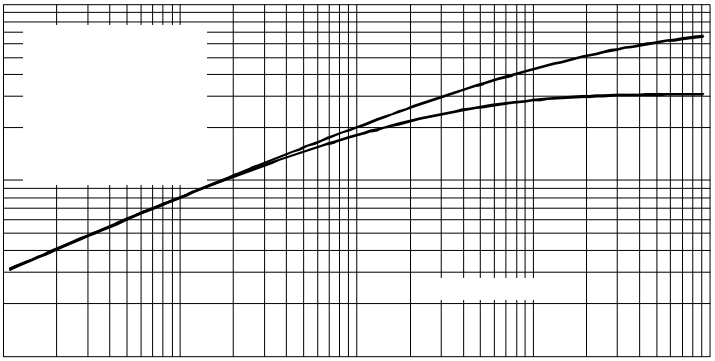


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

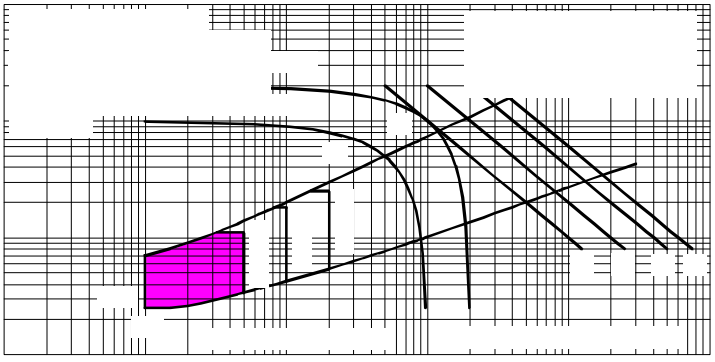


Fig. 11 - Gate Characteristics

Blocking

	Parameter	ST780C..L	Units	Conditions
dv/dt	Maximum critical rate of rise of off-state voltage	500	V/µs	$T_J = T_J$ max. linear to 80% rated V_{DRM}
I_{DRM} I_{RRM}	Max. peak reverse and off-state leakage current	80	mA	$T_J = T_J$ max, rated V_{DRM}/V_{RRM} applied

Triggering

	Parameter	ST780C..L		Units	Conditions	
P_{GM}	Maximum peak gate power	10.0		W	$T_J = T_J$ max, $t_p \leq 5$ms	
$P_{G(AV)}$	Maximum average gate power	2.0		W	$T_J = T_J$ max, f = 50Hz, d% = 50	
I_{GM}	Max. peak positive gate current	3.0		A	$T_J = T_J$ max, $t_p \leq 5$ms	
$+V_{GM}$	Maximum peak positive gate voltage	20		V	$T_J = T_J$ max, $t_p \leq 5$ms	
$-V_{GM}$	Maximum peak negative gate voltage	5.0		V		
		TYP.	MAX.			
I_{GT}	DC gate current required to trigger	200	-	mA	T_J = - 40°C	Max. required gate trigger/ current/ voltage are the lowest value which will trigger all units 12V anode-to-cathode applied
		100	200		T_J = 25°C	
		50	-		T_J = 125°C	
V_{GT}	DC gate voltage required to trigger	2.5	-	V	T_J = - 40°C	
		1.8	3.0		T_J = 25°C	
		1.1	-		T_J = 125°C	
I_{GD}	DC gate current not to trigger	10		mA	$T_J = T_J$ max	Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied
V_{GD}	DC gate voltage not to trigger	0.25		V		

Thermal and Mechanical Specification

	Parameter	ST780C..L	Units	Conditions
T_J	Max. operating temperature range	-40 to 125	°C	
T_{stg}	Max. storage temperature range	-40 to 150	°C	
R_{thJ-hs}	Max. thermal resistance, junction to heatsink	0.073	K/W	DC operation single side cooled
		0.031	K/W	DC operation double side cooled
R_{thC-hs}	Max. thermal resistance, case to heatsink	0.011	K/W	DC operation single side cooled
		0.006	K/W	DC operation double side cooled
F	Mounting force, ± 10%	14700	N	
		(1500)	(Kg)	
wt	Approximate weight	255	g	
	Case style	TO - 200AC (B-PUK)		See Outline Table

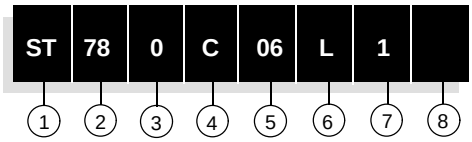
$\Delta R_{thJ\text{-}hs}$ Conduction

(The following table shows the increment of thermal resistence $R_{thJ\text{-}hs}$ when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	Single Side	Double Side	Single Side	Double Side		
180°	0.009	0.009	0.006	0.006	K/W	$T_J = T_J$ max.
120°	0.011	0.011	0.011	0.011		
90°	0.014	0.014	0.015	0.015		
60°	0.020	0.020	0.021	0.021		
30°	0.036	0.036	0.036	0.036		

Ordering Information Table

Device Code



1 - Thyristor

2 - Essential part number

3 - 0 = Converter grade

4 - C = Ceramic Puk

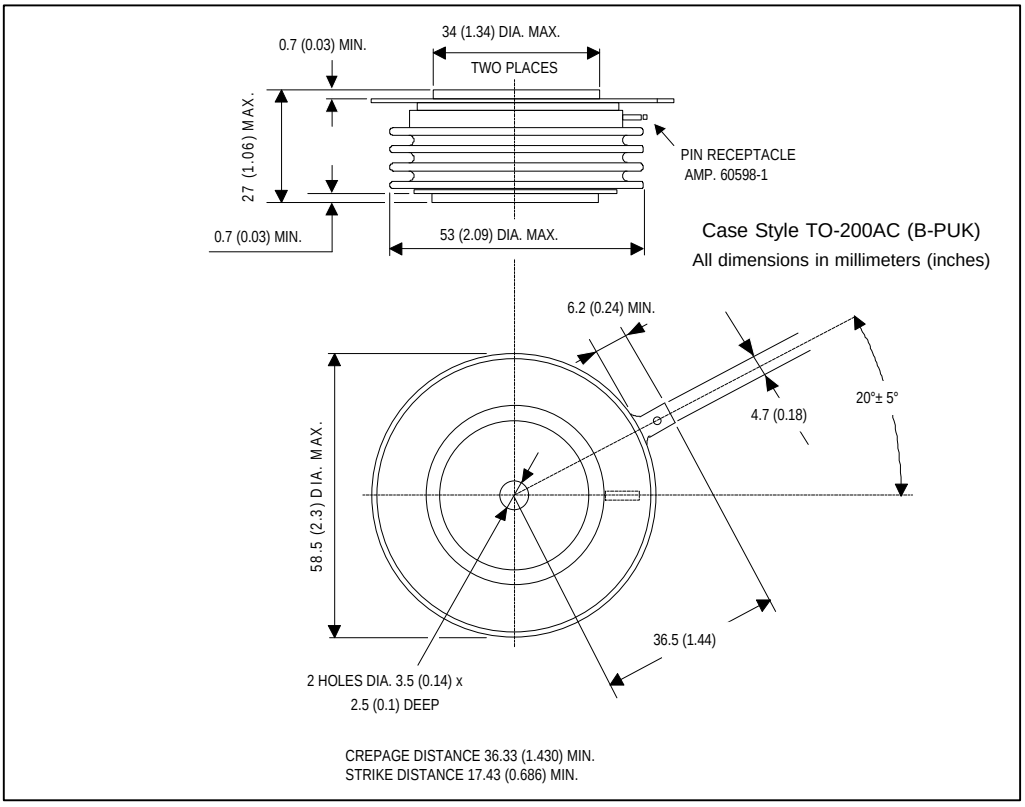
5 - Voltage code: Code x 100 = V_{RRM} (See Voltage Rating Table)

6 - L = Puk Case TO-200AC (B-PUK)

7 - 0 = Eyelet terminals (Gate and Auxiliary Cathode Unsoldered Leads)
1 = Fast-on terminals (Gate and Auxiliary Cathode Unsoldered Leads)
2 = Eyelet terminals (Gate and Auxiliary Cathode Soldered Leads)
3 = Fast-on terminals (Gate and Auxiliary Cathode Soldered Leads)

8 - Critical dv/dt: None = 500V/µsec (Standard selection)
L = 1000V/µsec (Special selection)

Outline Table



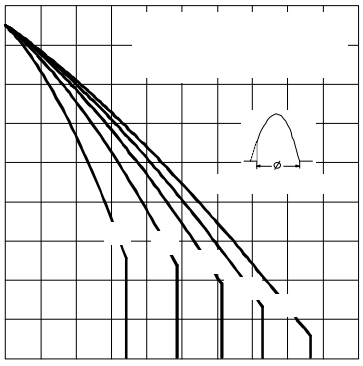


Fig. 1 - Current Ratings Characteristics

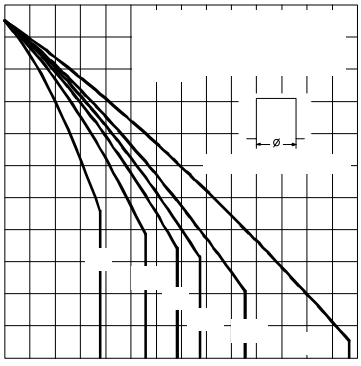


Fig. 2 - Current Ratings Characteristics